

IN THE CLAIMS:

1. (Cancelled)

2. (Cancelled)

3. (Currently Amended) The display device of claim [[2]] 6, wherein a selective transistor is connected between said nonvolatile data holding section and said control line, and a gate of said selective transistor is connected to a selective line.

4. (Cancelled)

5. (Cancelled)

6. (Currently Amended) A The display device, comprising:
~~of claim 2, wherein said control element and said nonvolatile data holding section~~
~~are formed of a transistor having~~
a display element;

an MFMIS structure in which transistor which has a first metal layer, a ferroelectric capacitor is connected to the gate side of a MOS transistor through a common electrode or a wiring, layer, a second metal layer for gate electrode and an insulator layer provided on a semiconductor layer, a source and drain of said MFMIS structure transistor being connected to said display element and a driving line and said first metal layer being connected to a control line; and

a capacitor is connected between ~~a connecting portion of a gate electrode of said MOS transistor with said ferroelectric capacitor~~ said second metal layer and a ground or a write line,

wherein the control data ~~can be~~ is written to said ~~nonvolatile data holding section~~ MFMIS structure transistor by using said control line and said ground or said write line.

7. (Cancelled)

8. (Cancelled)

9. (Currently Amended) The display device of claim ~~[[2]]~~ 6, wherein said display element is formed by an organic EL element.

10. (Cancelled)

11. (Currently Amended) A The display device, comprising:
a display element;

~~of claim 2, wherein said control element is formed of a MOS transistor, said nonvolatile data holding section is formed of~~ a source and drain of said MOS transistor being connected to said display element and a driving line;

a ferroelectric capacitor ~~which is connected to~~ between a gate of said MOS transistor ~~type element, and a control line;~~ and

a capacitor is connected between a ~~connecting portion of~~ said gate with said ~~ferroelectric capacitor~~ and a ground or a write line,

wherein the control data is written to said ~~nonvolatile data holding section~~ ferroelectric capacitor by using said control line and said ground or said write line.

12. (New) The display device of claim 11, wherein a selective transistor is connected between said ferroelectric capacitor and said control line, and a gate of said selective transistor is connected to a selective line.

13. (New) The display device of claim 11, wherein said display element is formed by an organic EL element.

14. (New) A display device, comprising:

a display element;

a control element for controlling a voltage or a current to be applied to said display element to drive said display element; and

a nonvolatile data holding section integrated with said control element or connected to said control element and capable of holding control data of said control element in a floating state;

wherein said nonvolatile data holding section is constituted by an element utilizing a magnetoresistance effect or a single electron memory.

15. (New) The display device of claim 14, wherein said display element is formed by an organic EL element.